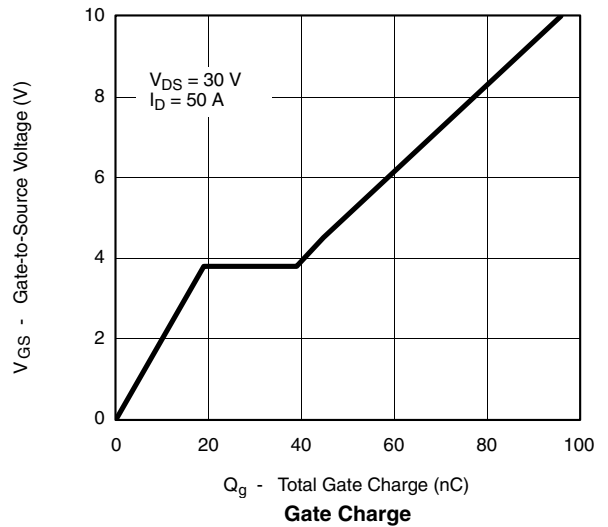
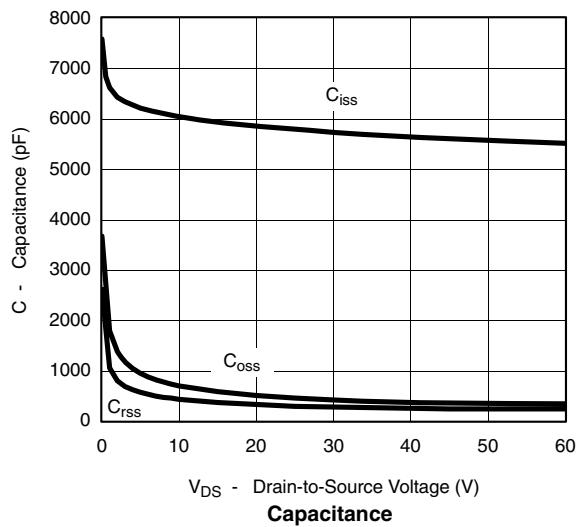
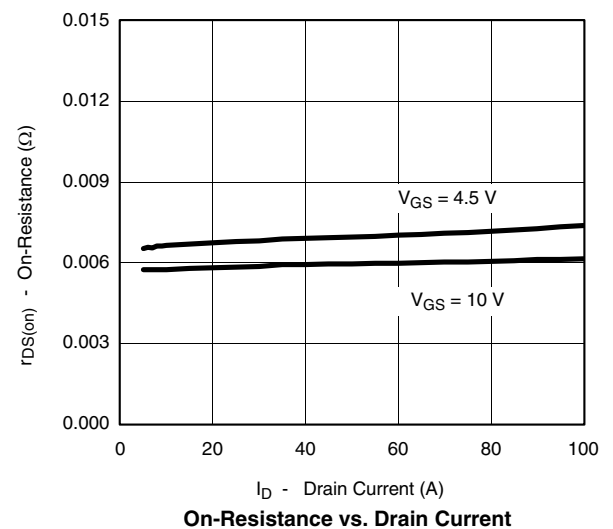
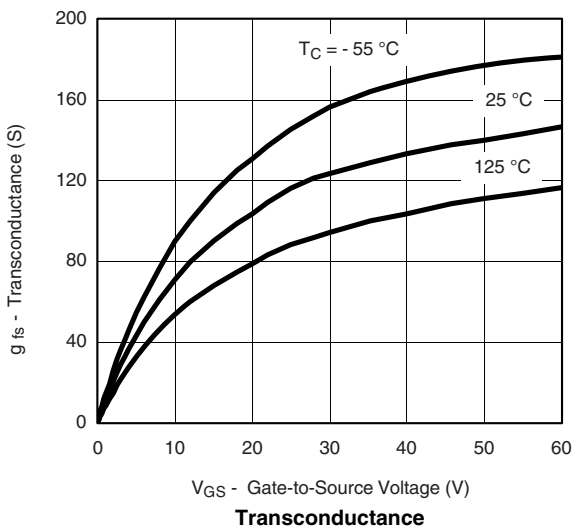
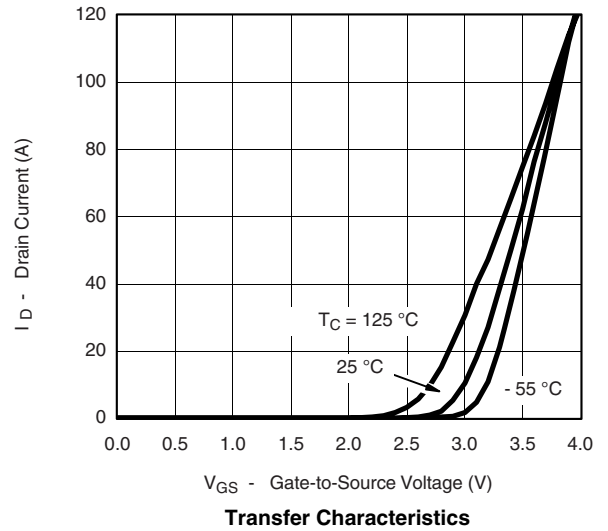
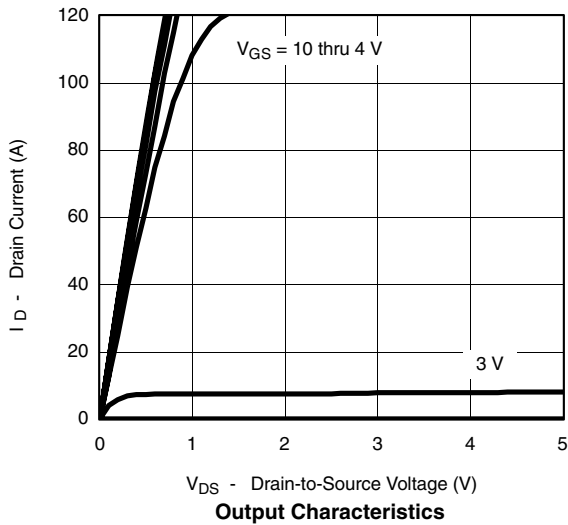


SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 175\text{ }^{\circ}\text{C}$			150	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}$ , $V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$		0.0061	0.0074	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$			0.0122	
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 175\text{ }^{\circ}\text{C}$			0.0148	
		$V_{GS} = 4.5\text{ V}$ , $I_D = 20\text{ A}$		0.0071	0.0088	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 15\text{ A}$	20	80		S
Dynamic <sup>b</sup>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		5800		pF
Output Capacitance	$C_{oss}$			450		
Reversen Transfer Capacitance	$C_{rss}$			300		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 50\text{ A}$		96	144	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			19		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			20		
Gate Resistance	$R_g$			1.5		$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}$ , $R_L = 0.6\text{ }\Omega$ $I_D \cong 50\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time <sup>c</sup>	$t_r$			13	20	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			62	95	
Fall Time <sup>c</sup>	$t_f$			14	25	
Source-Drain Diode Ratings and Characteristics ( $T_C = 25\text{ }^{\circ}\text{C}$ ) <sup>b</sup>						
Continuous Current	$I_S$				50	A
Pulsed Current	$I_{SM}$				100	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 30\text{ A}$ , $V_{GS} = 0\text{ V}$		0.90	1.50	V
Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		37	55	ns

## Notes:

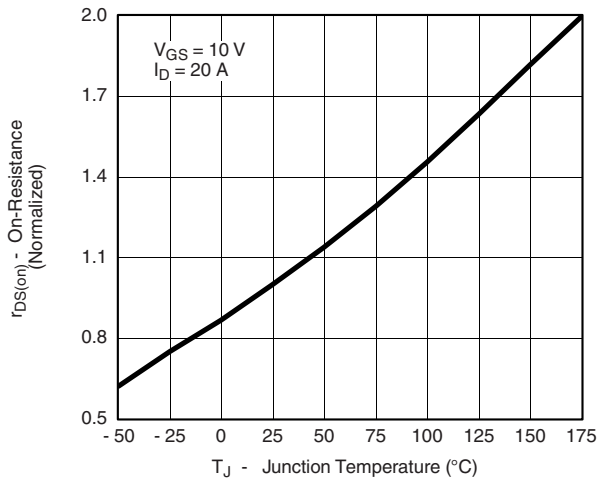
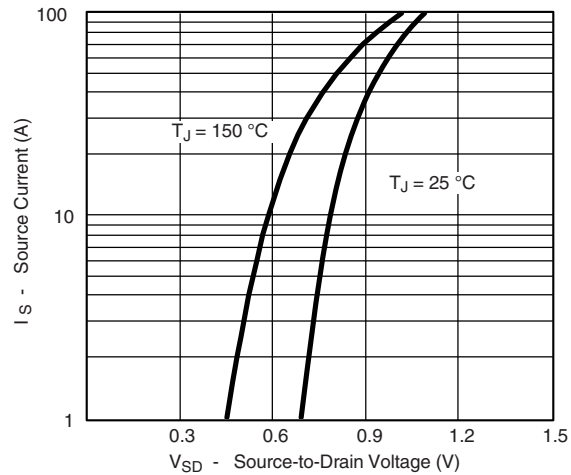
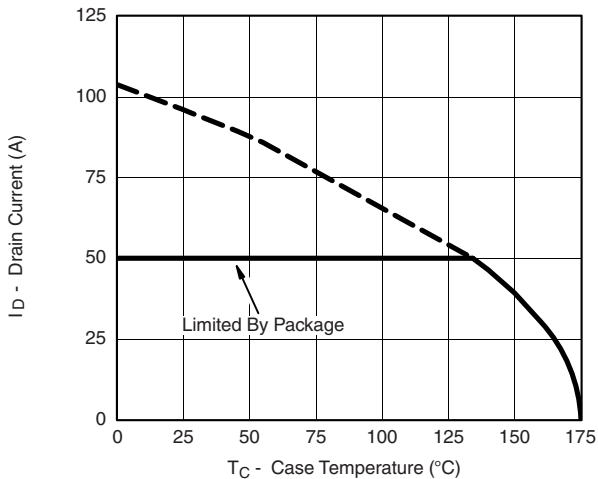
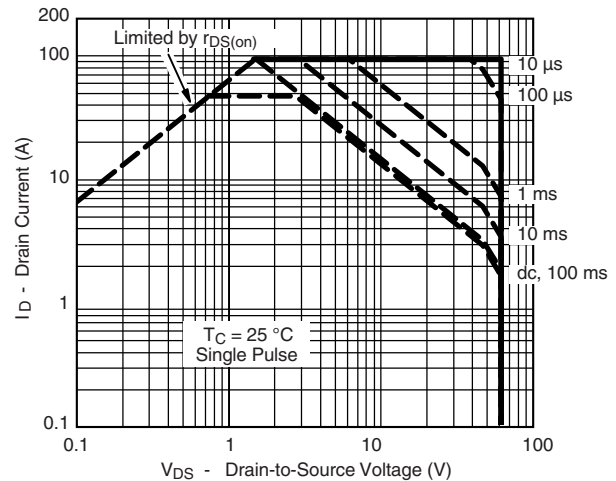
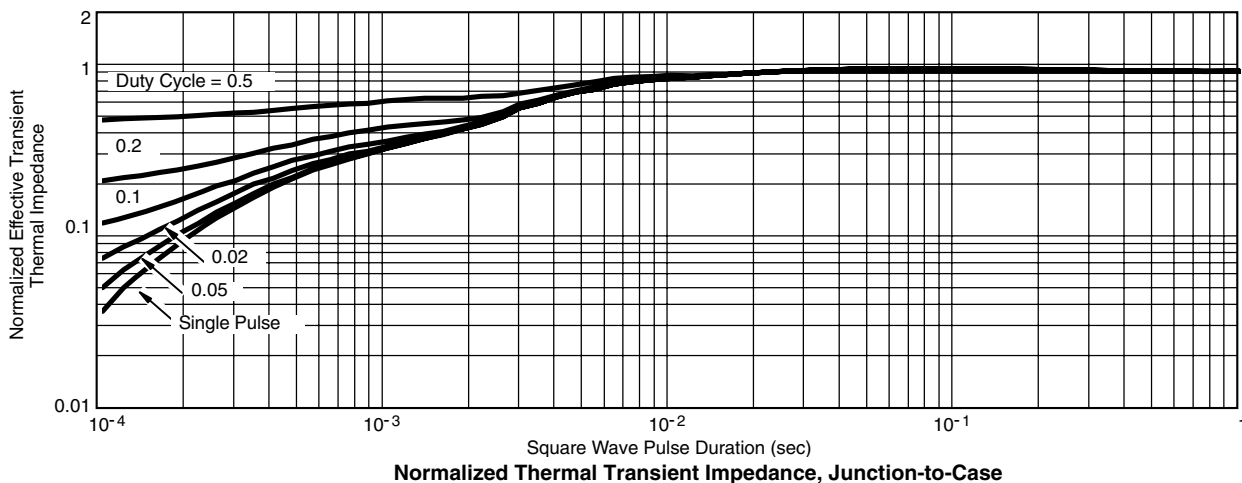
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C unless noted

**SUD50N06-07L**

Vishay Siliconix

**TYPICAL CHARACTERISTICS** 25 °C unless noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****THERMAL RATINGS****Maximum Avalanche and Drain Current vs. Case Temperature****Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72953>.



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